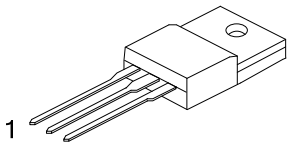
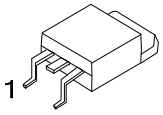
8.0A, 500V N-CHANNEL SUPER-JUNCTION MOSFET



TO-220F1



TO-252

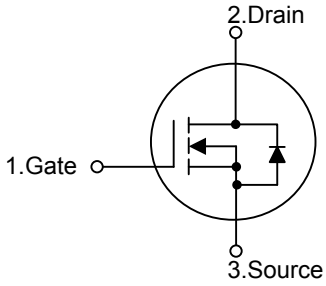
■ DESCRIPTION

The **UTC 8NM50** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

* $R_{DS(ON)}$ < 0.49Ω @ V_{GS}=10V, I_D=4.0A
* High Switching Speed
* 100% Avalanche Tested

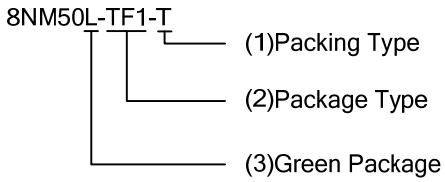
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8NM50L-TF1-T	8NM50G-TF1-T	TO-220F1	G	D	S	Tube
8NM50L-TN3-R	8NM50G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

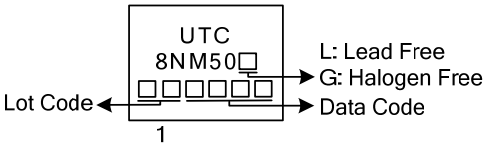


(1) T: Tube, R: Tape Reel

(2) TF1: TO-220F1, TN3: TO-252

(3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	8.0	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Current (Note 2)		I_{AR}	3.9	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	236	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	8.0	V/ns
Power Dissipation	TO-220F1	P_D	42	W
	TO-252		80	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 31mH, I_{AS} = 3.9A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 8.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

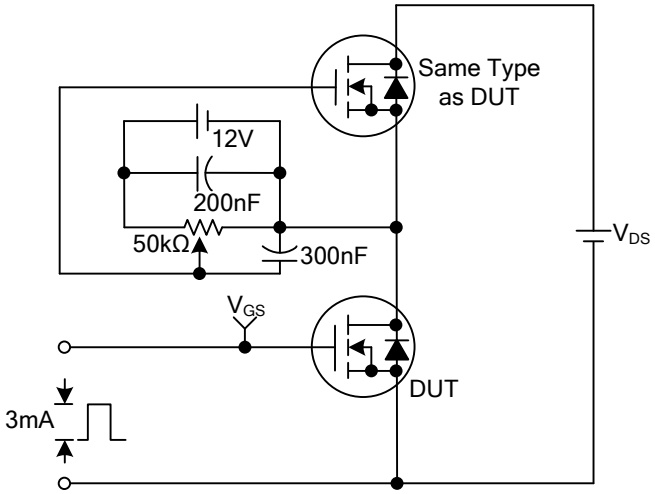
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1	θ_{JA}	62.5	°C/W
	TO-252		110	°C/W
Junction to Case	TO-220F1	θ_{JC}	3	°C/W
	TO-252		1.56	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise noted)

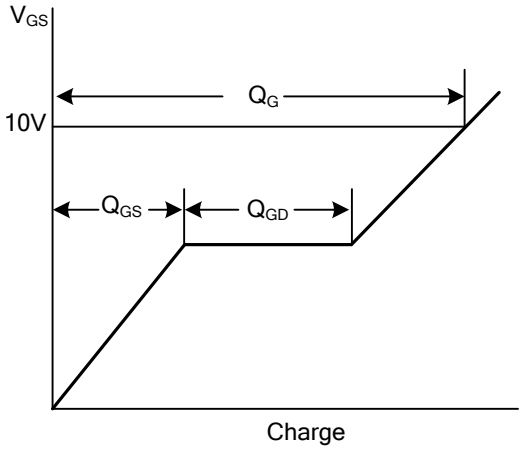
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	500			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=500V, V_{GS}=0V			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=4.0A			0.49	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		460		pF
Output Capacitance		C_{OSS}			430		pF
Reverse Transfer Capacitance		C_{RSS}			62		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=50V, I_D=1.3A, I_G=100μA V_{GS}=10V (Note 1,2)		30		nC
Gate to Source Charge		Q_{GS}			3		nC
Gate to Drain Charge		Q_{GD}			13		nC
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$	V_{DD} =30V, I_D =0.5A, R_G =25Ω, V_{GS}=10V (Note 1,2)		50		ns
Rise Time		t_R			104		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			182		ns
Fall-Time		t_F			93		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				8.0	A
Maximum Body-Diode Pulsed Current		I_{SM}				32	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S=8.0A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S=8.0A, V_{GS}=0V, dI_F/dt=100A/μs		270		ns
Body Diode Reverse Recovery Charge		Q_{rr}			3.05		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

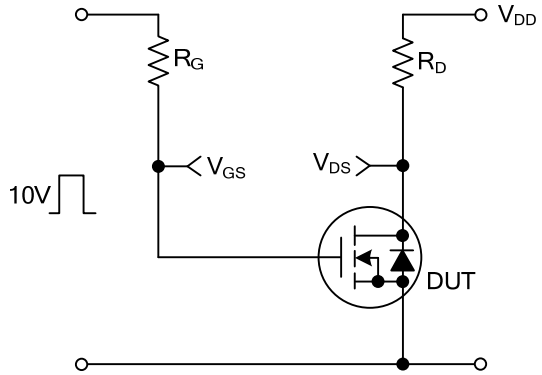
■ TEST CIRCUITS AND WAVEFORMS



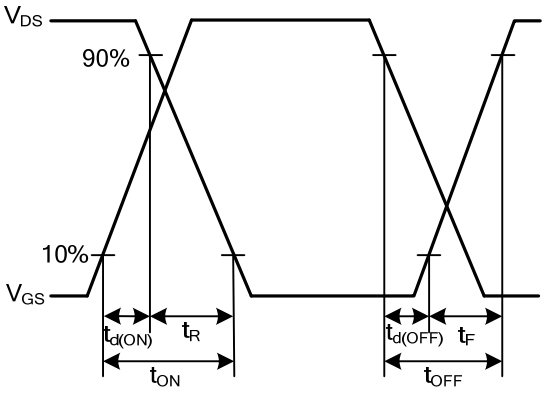
Gate Charge Test Circuit



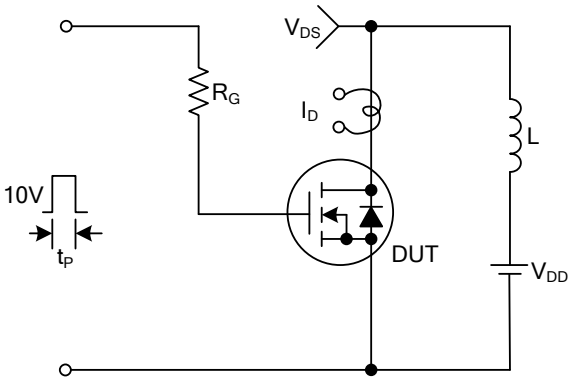
Gate Charge Waveforms



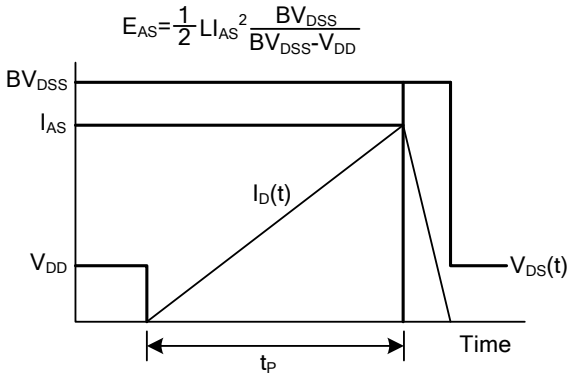
Resistive Switching Test Circuit



Resistive Switching Waveforms

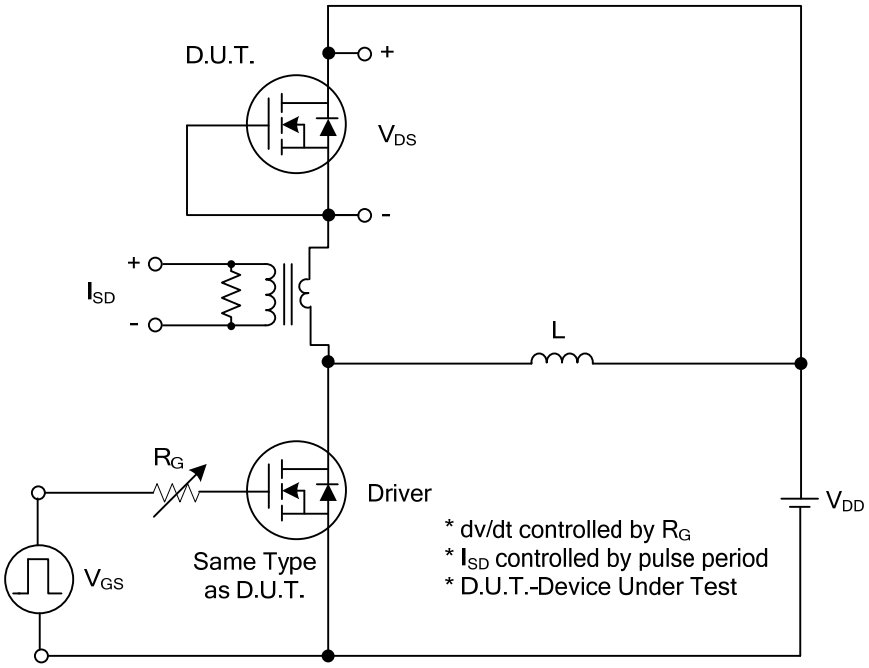


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)



Peak Diode Recovery dv/dt Test Circuit & Waveforms